

IPB120N06S4-H1-VB Datasheet

N-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY

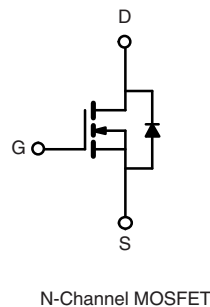
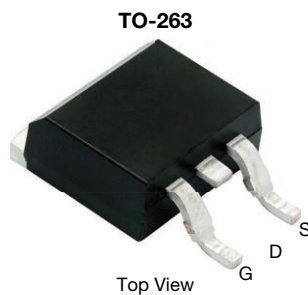
V_{DS} (V)	60
$R_{DS(on)}$ (Ω) at $V_{GS} = 10$ V	0.0025
$R_{DS(on)}$ (Ω) at $V_{GS} = 4.5$ V	0.0070
I_D (A)	270
Configuration	Single

FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- 100 % R_g and UIS tested



RoHS
COMPLIANT
HALOGEN
FREE



ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	$T_C = 25$ °C	A
		$T_C = 125$ °C	
Continuous Source Current (Diode Conduction)	I_S	120 ^a	
Pulsed Drain Current ^b	I_{DM}	600	
Single Pulse Avalanche Current	I_{AS}	75	
Single Pulse Avalanche Energy	E_{AS}	281	mJ
Maximum Power Dissipation ^b	P_D	$T_C = 25$ °C	W
		$T_C = 125$ °C	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient	R_{thJA}	40	°C/W
Junction-to-Case (Drain)	R_{thJC}	0.4	

Notes

- Package limited.
- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR4 material).

SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		60	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		1.5	2.0	2.5	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 60 V	-	-	1	μA
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 125 °C	-	-	50	
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 175 °C	-	-	1.5	mA
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	120	-	-	A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 30 A	-	0.0025	-	Ω
		V _{GS} = 10 V	I _D = 30 A, T _J = 125 °C	-	0.0040	-	
		V _{GS} = 10 V	I _D = 30 A, T _J = 175 °C	-	0.0075	-	
		V _{GS} = 4.5 V	I _D = 20 A	-	0.0070	-	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 30 A		-	164	-	S
Dynamic ^b							
Input Capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	-	9000	-	pF
Output Capacitance	C _{oss}			-	5750	7200	
Reverse Transfer Capacitance	C _{rss}			-	860	1100	
Total Gate Charge ^c	Q _g	V _{GS} = 10 V	V _{DS} = 30 V, I _D = 80 A	-	128	200	nC
Gate-Source Charge ^c	Q _{gs}			-	33	-	
Gate-Drain Charge ^c	Q _{gd}			-	11	-	
Gate Resistance	R _g	f = 1 MHz		0.8	1.68	2.6	Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 30 V, R _L = 0.375 Ω I _D ≅ 80 A, V _{GEN} = 10 V, R _g = 1 Ω		-	20	25	ns
Rise Time ^c	t _r			-	15	40	
Turn-Off Delay Time ^c	t _{d(off)}			-	65	100	
Fall Time ^c	t _f			-	12	20	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	2 0 0	A
Forward Voltage	V _{SD}	I _F = 80 A, V _{GS} = 0 V		-	0.88	1.5	V

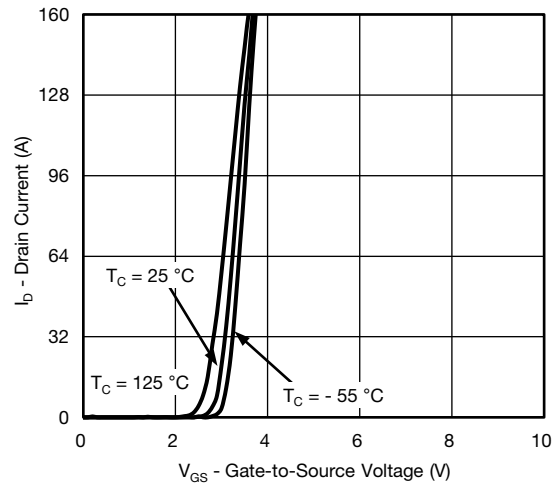
Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



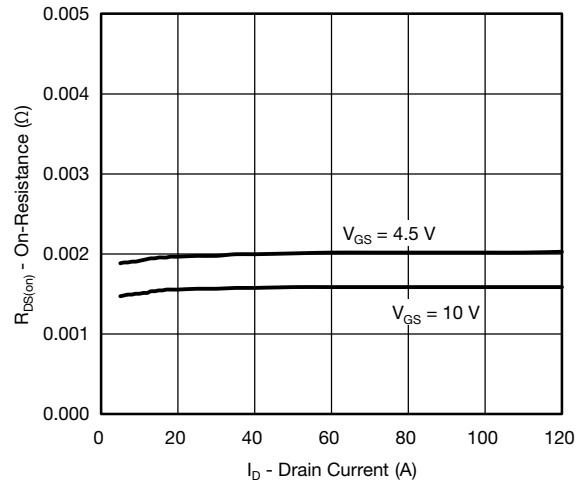
Output Characteristics



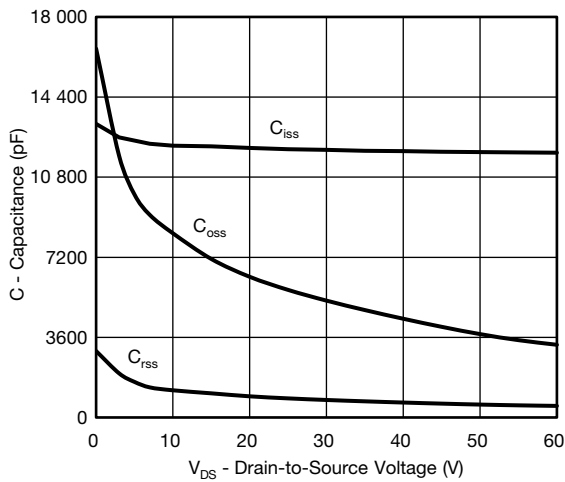
Transfer Characteristics



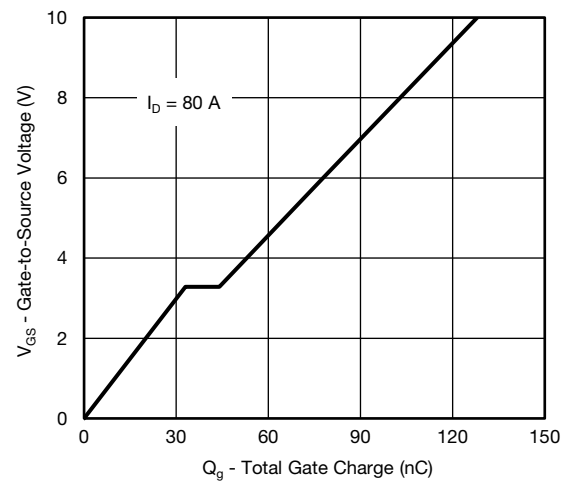
Transconductance



On-Resistance vs. Drain Current



Capacitance

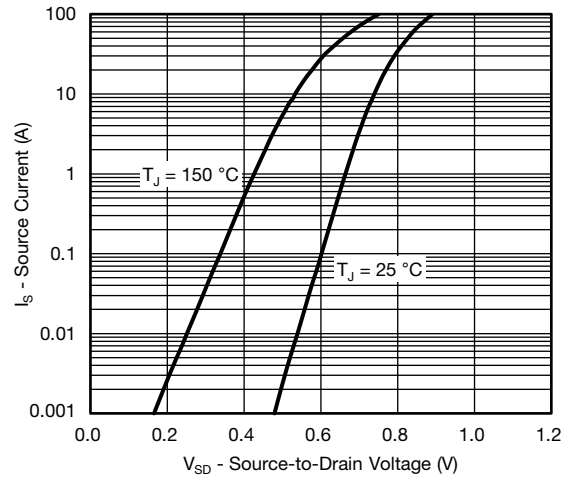


Gate Charge

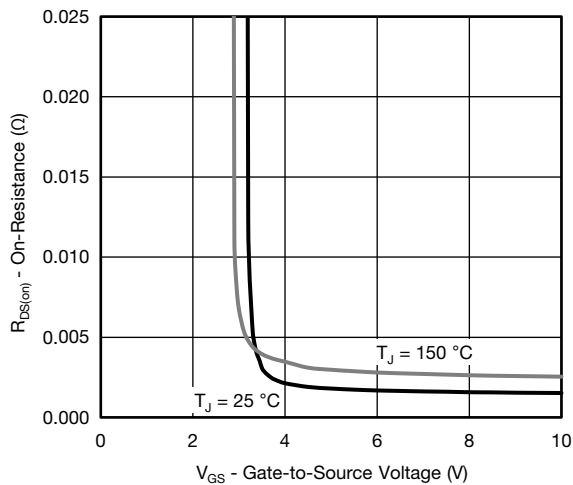
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



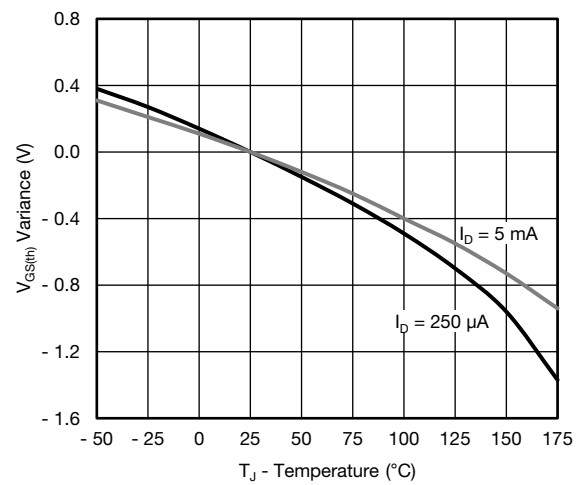
On-Resistance vs. Junction Temperature



Source Drain Diode Forward Voltage



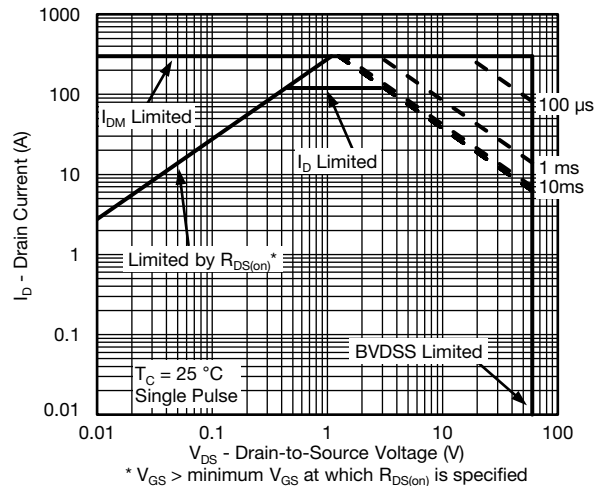
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Drain Source Breakdown vs. Junction Temperature



Safe Operating Area

* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

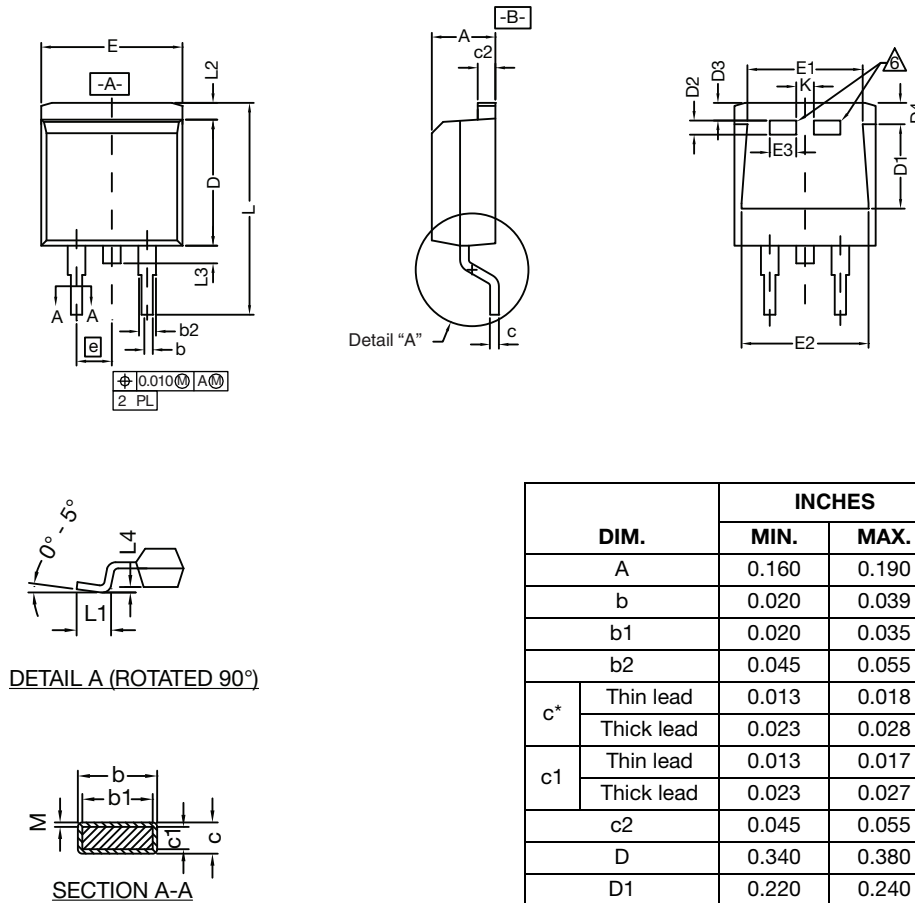
THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Normalized Thermal Transient Impedance, Junction-to-Ambient

Normalized Thermal Transient Impedance, Junction-to-Case
Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^{\circ}\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Case ($25\text{ }^{\circ}\text{C}$)
- are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

TO-263 (D²PAK): 3-LEAD



Notes

1. Plane B includes maximum features of heat sink tab and plastic.
2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
3. Pin-to-pin coplanarity max. 4 mils.
4. *: Thin lead is for SUB, SYB.
Thick lead is for SUM, SYM, SQM.
5. Use inches as the primary measurement.
6. This feature is for thick lead.

DIM.		INCHES		MILLIMETERS	
		MIN.	MAX.	MIN.	MAX.
A		0.160	0.190	4.064	4.826
b		0.020	0.039	0.508	0.990
b1		0.020	0.035	0.508	0.889
b2		0.045	0.055	1.143	1.397
c*	Thin lead	0.013	0.018	0.330	0.457
	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
	Thick lead	0.023	0.027	0.584	0.685
c2		0.045	0.055	1.143	1.397
D		0.340	0.380	8.636	9.652
D1		0.220	0.240	5.588	6.096
D2		0.038	0.042	0.965	1.067
D3		0.045	0.055	1.143	1.397
D4		0.044	0.052	1.118	1.321
E		0.380	0.410	9.652	10.414
E1		0.245	-	6.223	-
E2		0.355	0.375	9.017	9.525
E3		0.072	0.078	1.829	1.981
e		0.100 BSC		2.54 BSC	
K		0.045	0.055	1.143	1.397
L		0.575	0.625	14.605	15.875
L1		0.090	0.110	2.286	2.794
L2		0.040	0.055	1.016	1.397
L3		0.050	0.070	1.270	1.778
L4		0.010 BSC		0.254 BSC	
M		-	0.002	-	0.050
ECN: T13-0707-Rev. K, 30-Sep-13					
DWG: 5843					

RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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